



100V N-Channel Enhancement Mode MOSFET

Voltage

100 V

Current

18A

Features

- RDS(ON), VGS@10V, ID@18A< $50m\Omega$
- RDS(ON), VGS@4.5V, ID@15A<55mΩ
- Advanced Trench Process Technology
- High density cell design for ultra low on-resistance
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

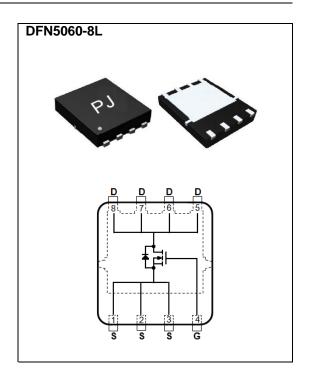
Mechanical Data

• Case: DFN5060-8L Package

• Terminals: Solderable per MIL-STD-750, Method 2026

Approx. Weight: 0.0028 ounces, 0.08 grams

Marking: Q5474A



Maximum Ratings and Thermal Characteristics (T_A=25°C unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		V_{DS}	100	V
Gate-Source Voltage		V_{GS}	<u>+</u> 20	V
Continuous Drain Current		I _D	18	Α
Pulsed Drain Current		I _{DM}	36	Α
Single Pulse Avalanche Energy (Note 5)		E _{AS}	16.2	mJ
Power Dissipation	T _C =25°C	P_D	52	W
	Derate above 25°C		416	mW/°C
Operating Junction and Storage Temperature Range		T_J, T_{STG}	-55~150	°C
Typical Thermal resistance - Junction to Ambient, t<10s (Note 3)		$R_{ heta JC}$	2.4	°C/W





Electrical Characteristics (T_A=25 °C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS		
Static								
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V,I _D =250uA	100	-	-	V		
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_{D}=250uA$	1.0	1.5	2.5	V		
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =10V,I _D =18A	-	37	50	mΩ		
		V _{GS} =4.5V,I _D =15A	-	38	55			
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =80V,V _{GS} =0V	-	0.03	1.0	uA		
Gate-Source Leakage Current	I_{GSS}	V _{GS} = <u>+</u> 20V,V _{DS} =0V	-	<u>+</u> 10	<u>+</u> 100	nA		
Dynamic (Note 7)								
Total Gate Charge	Q_g	V _{DS} =80V, I _D =18A, V _{GS} =10V (Note 1,2)	-	61	-	nC		
Gate-Source Charge	Q_gs		-	8.8	-			
Gate-Drain Charge	Q_gd		-	11	-			
Input Capacitance	Ciss	V _{DS} =15V, V _{GS} =0V, f=1.0MHZ	-	3555	-	pF		
Output Capacitance	Coss		-	119	-			
Reverse Transfer Capacitance	Crss		-	56	-			
Turn-On Delay Time	td _(on)	V_{DD} =50V, I_{D} =18A, V_{GS} =10V, R_{G} =3.3 Ω (Note 1,2)	-	16	-	ns		
Turn-On Rise Time	tr		-	50	-			
Turn-Off Delay Time	td _(off)		-	64	-			
Turn-Off Fall Time	tf		-	18	-			
Drain-Source Diode								
Maximum Continuous Drain-Source				-	18	А		
Diode Forward Current	I _S		_					
Diode Forward Voltage	V _{SD}	I _S =1.0A, V _{GS} =0V	-	0.7	1.2	V		

NOTES:

- 1. Pulse width<a>300us, Duty cycle<a>2%
- 2. Essentially independent of operating temperature typical characteristics.
- 3. The maximum current rating is package limited.
- 4. Repetitive rating, pulse width limited by junction temperature TJ(MAX)=150°C. Ratings are based on low frequency and duty cycles to keep initial TJ =25°C.
- 5. The test condition is L=0.1mH, I_{AS} =18A, V_{DD} =25V, V_{GS} =10V
- 6. Rejah is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper.
- 7. Guaranteed by design, not subject to production testing.





TYPICAL CHARACTERISTIC CURVES

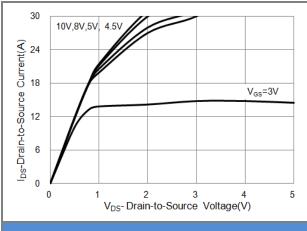


Fig.1 On-Region Characteristics

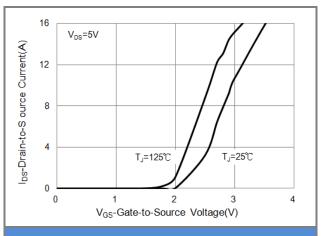


Fig.2 Transfer Characteristics

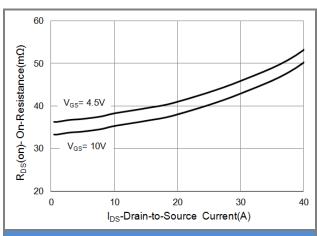


Fig.3 On-Resistance vs. Drain Current

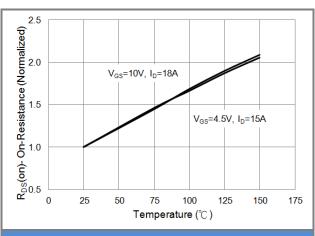


Fig.4 On-Resistance vs. Junction temperature

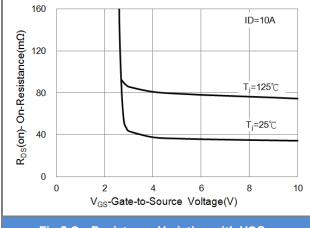
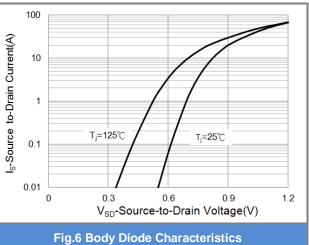


Fig.5 On-Resistance Variation with VGS.







TYPICAL CHARACTERISTIC CURVES

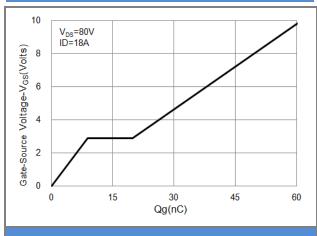


Fig.7 Gate-Charge Characteristics

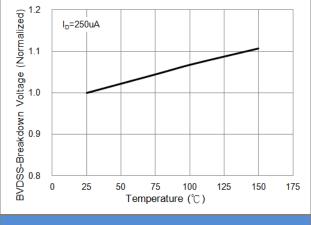


Fig.8 Breakdown Voltage Variation vs. Temperature

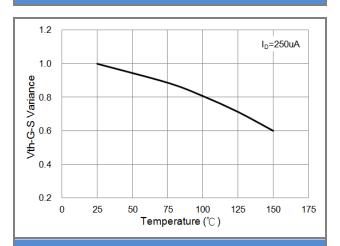


Fig.9 Threshold Voltage Variation with Temperature.

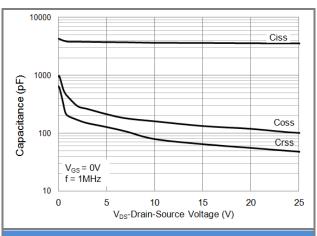
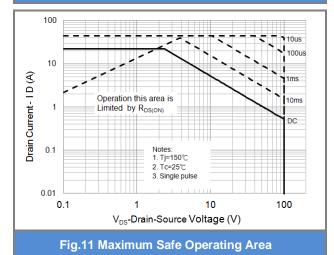


Fig.10 Capacitance vs. Drain-Source Voltage.







TYPICAL CHARACTERISTIC CURVES

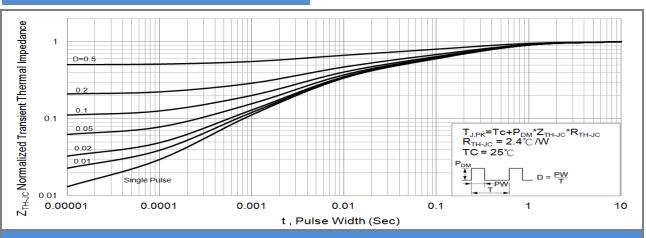


Fig.12 Normalized Transient Thermal Impedance vs. Pulse Width

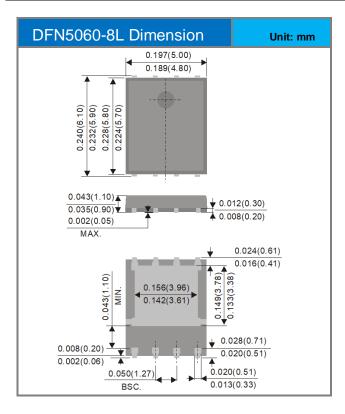


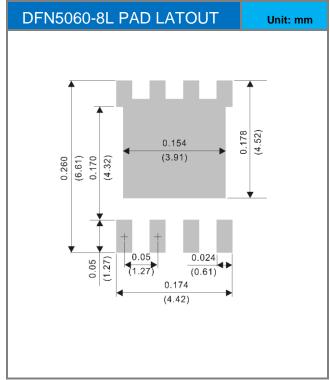


PART NO PACKING CODE VERSION

Part No Packing Code	Package Type	Packing type	Marking	Version
PJQ5474A_R2_00001	DFN5060-8L	3000pcs / 13" reel	Q5474A	Halogen free

Packaging Information & Mounting Pad Layout









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